

Silicon PNP Power Transistors

2SA1987

DESCRIPTION

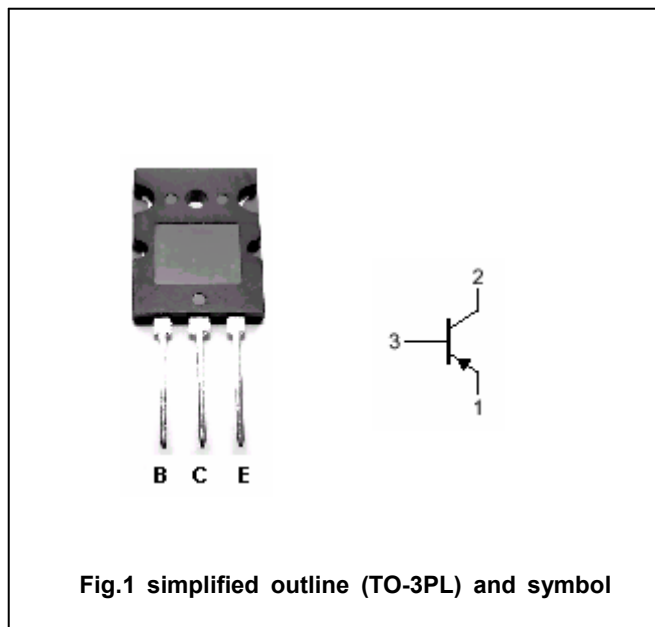
- With TO-3PL package
- Complement to type 2SC5359
- High collector voltage

APPLICATIONS

- Power amplifier applications
- Recommended for 100W high fidelity audio frequency amplifier output stage

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-230	V
V_{CEO}	Collector-emitter voltage	Open base	-230	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-15	A
I_B	Base current		-1.5	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	180	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-50mA ; I_B=0$	-230			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-8A ; I_B=-0.8A$		-1.5	-3.0	V
V_{BE}	Base-emitter voltage	$I_C=-7A ; V_{CE}=-5V$		-1.0	-1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=-230V ; I_E=0$			-5	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-5V ; I_C=0$			-5	μA
h_{FE-1}	DC current gain	$I_C=-1A ; V_{CE}=-5V$	55		160	
h_{FE-2}	DC current gain	$I_C=-7A ; V_{CE}=-5V$	35			
f_T	Transition frequency	$I_C=-1A ; V_{CE}=-5V$		30		MHz
C_{OB}	Collector output capacitance	$I_E=0, f=1MHz ; V_{CB}=-10V$		360		pF

◆ h_{FE-1} classifications

R	O
55-110	80-160

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PACKAGE OUTLINE

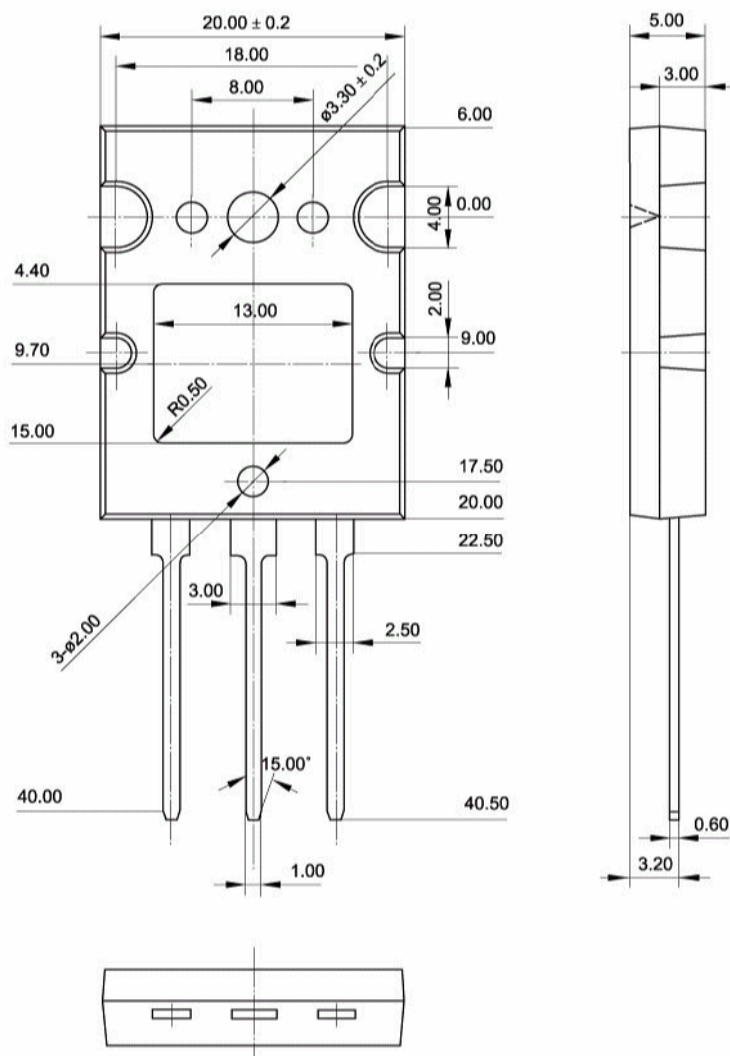


Fig.2 Outline dimensions (unindicated tolerance:±0.50 mm)